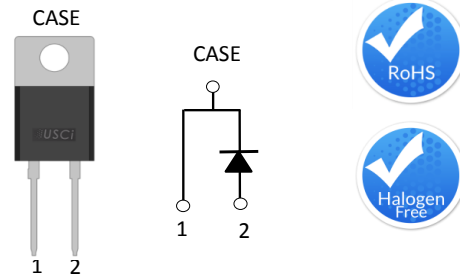


## Description

United Silicon Carbide, Inc. offers the xR series of high performance SiC Schottky diodes. With zero reverse recovery charge and 175°C maximum junction temperature, USCI's diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



| Part Number | Package   | Marking   |
|-------------|-----------|-----------|
| UJ2D1215T   | TO-220-2L | UJ2D1215T |

## Features

- ◆ Positive temperature coefficient for safe operation and ease of paralleling
- ◆ 175°C maximum operating junction temperature
- ◆ Extremely fast switching not dependent on temperature
- ◆ Essentially no reverse or forward recovery
- ◆ RoHS compliant

## Typical Applications

- ◆ Power converters
- ◆ Industrial motor drives
- ◆ Switching-mode power supplies
- ◆ Power factor correction modules

## Maximum Ratings

| Parameter  | Symbol         | Test Conditions   | Value      | Units            |
|--|----------------|---|------------|------------------|
| DC blocking voltage  | $V_R$          |   | 1200       | V                |
| Repetitive peak reverse voltage, $T_j=25^\circ\text{C}$        | $V_{RRM}$      |   | 1200       | V                |
| Surge peak reverse voltage                                     | $V_{RSM}$      |   | 1200       | V                |
| Maximum DC forward current                                     | $I_F$          | $T_C = 138^\circ\text{C}$   | 15         | A                |
| Non-repetitive forward surge current<br>sine halfwave          | $I_{FSM}$      | $T_C = 25^\circ\text{C}, t_p = 10\text{ms}$                                     | 112.5      | A                |
|  |                | $T_C = 110^\circ\text{C}, t_p = 10\text{ms}$                                    | 90         |                  |
| Repetitive forward surge current<br>sine halfwave, $D=0.1$     | $I_{FRM}$      | $T_C = 25^\circ\text{C}, t_p = 10\text{ms}$                                     | 51.2       | A                |
|  |                | $T_C = 110^\circ\text{C}, t_p = 10\text{ms}$                                    | 31.3       |                  |
| Non-repetitive avalanche energy                                | $E_{AS}$       | $T_j = 25^\circ\text{C}, L = 10\text{mH}, I_{pk}=5\text{A}, V_{DD}=100\text{V}$ | 132        | mJ               |
| Power dissipation  | $P_{Tot}$      | $T_C = 25^\circ\text{C}$  | 187        | W                |
|  |                | $T_C = 138^\circ\text{C}$   | 46         |                  |
| Maximum junction temperature                                   | $T_{j,max}$    |   | 175        | $^\circ\text{C}$ |
| Operating and storage temperature                              | $T_j, T_{STG}$ |   | -55 to 175 | $^\circ\text{C}$ |
| Soldering temperatures, wavesoldering only<br>allowed at leads | $T_{sold}$     | 1.6mm from case for<br>10s  | 260        | $^\circ\text{C}$ |

**Electrical Characteristics**

T<sub>J</sub> = +25°C unless otherwise specified

| Parameter                              | Symbol         | Test Conditions                              | Value |      |      | Units |
|--|----------------|--|-------|------|------|-------|
|  |                |  | Min   | Typ  | Max  |       |
| Forward voltage                        | V <sub>F</sub> | I <sub>F</sub> = 15A, T <sub>J</sub> = 25°C  | -     | 1.5  | 1.7  | V     |
|  |                | I <sub>F</sub> = 15A, T <sub>J</sub> = 175°C | -     | 2.5  | 3    |       |
| Reverse current                        | I <sub>R</sub> | V <sub>R</sub> =1200V, T <sub>J</sub> =25°C  | -     | 45   | 375  | μA    |
|  |                | V <sub>R</sub> =1200V, T <sub>J</sub> =175°C | -     | 90   | 1000 |       |
| Total capacitive charge <sup>(2)</sup> | Q <sub>C</sub> | V <sub>R</sub> =800V                         |       | 69   |      | nC    |
| Total capacitance                      | C              | V <sub>R</sub> =1V, f=1MHz                   |       | 730  |      | pF    |
|  |                | V <sub>R</sub> =400V, f=1MHz                 |       | 64   |      |       |
|  |                | V <sub>R</sub> =800V, f=1MHz                 |       | 51   |      |       |
| Capacitance stored energy              | E <sub>C</sub> | V <sub>R</sub> =800V                         |       | 17.5 |      | μJ    |

(2) See Figure 8, Q<sub>c</sub> is independent on T<sub>J</sub>, di<sub>F</sub>/dt, and I<sub>F</sub> as shown in the application note USCi\_AN0011.

**Thermal characteristics**

| Parameter          | symbol           | Test Conditions | Value |     |     | Units |
|--------------------|------------------|-----------------|-------|-----|-----|-------|
|                    |                  |                 | Min   | Typ | Max |       |
| Thermal resistance | R <sub>θJC</sub> |                 |       | 0.6 | 0.8 | °C/W  |

**Typical Performance**

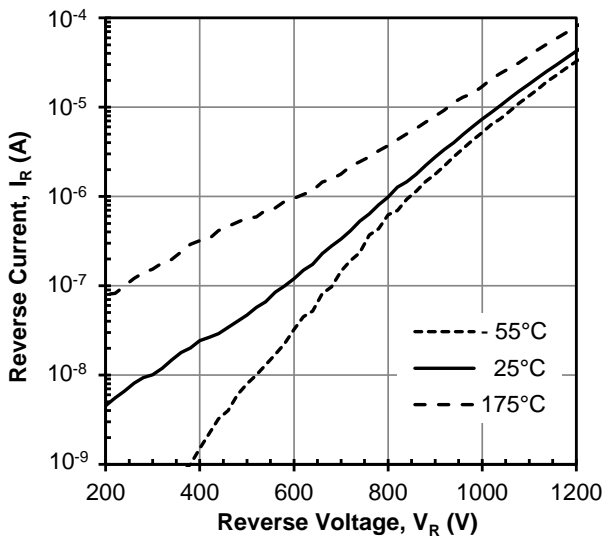


Figure 1 Typical reverse characteristics

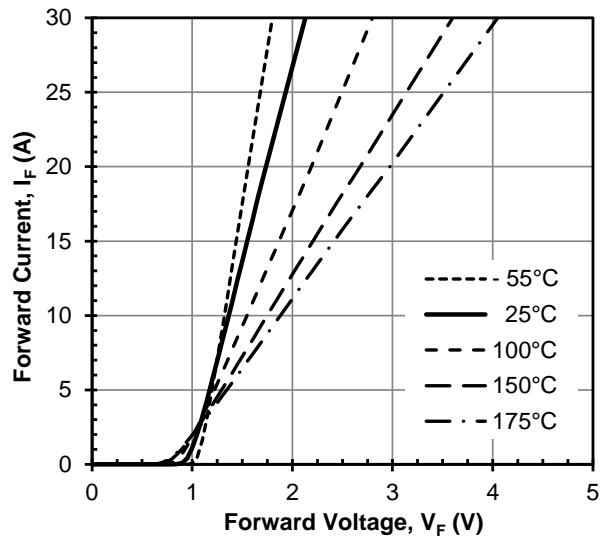


Figure 2 Typical forward characteristics

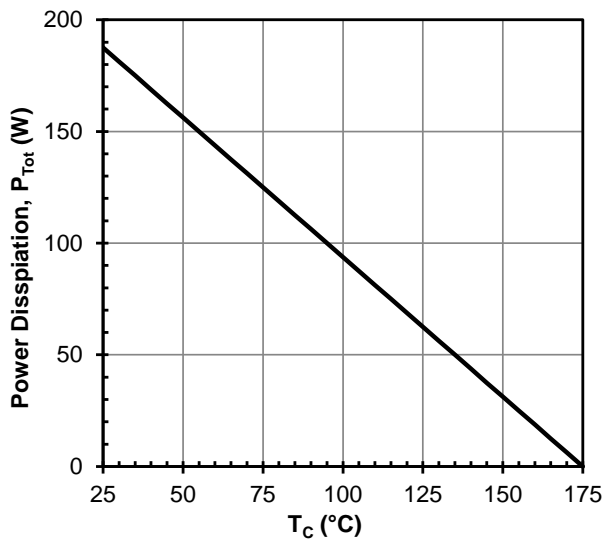


Figure 3 Power dissipation

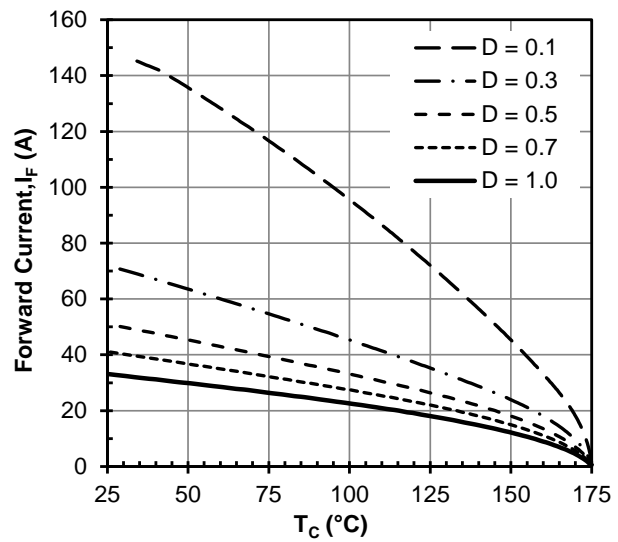


Figure 4 Diode forward current

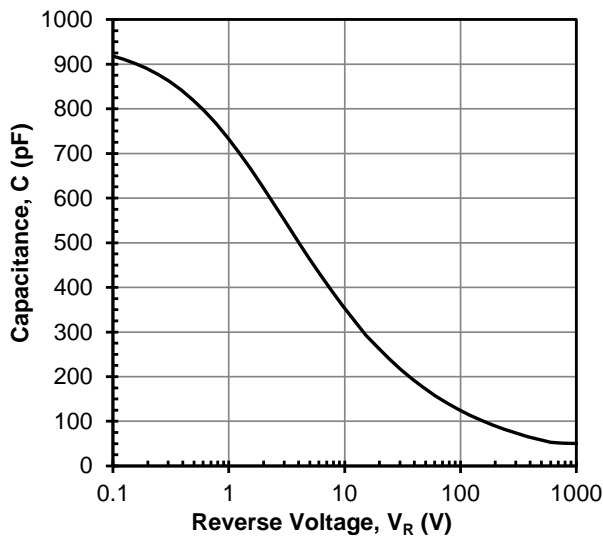


Figure 5 Capacitance vs. reverse voltage

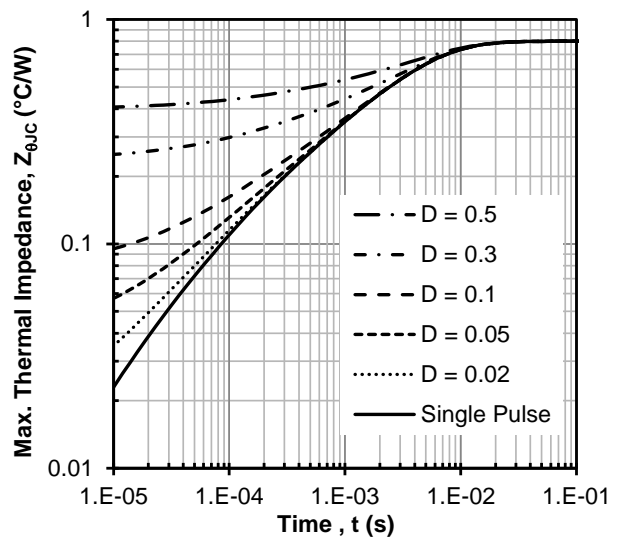
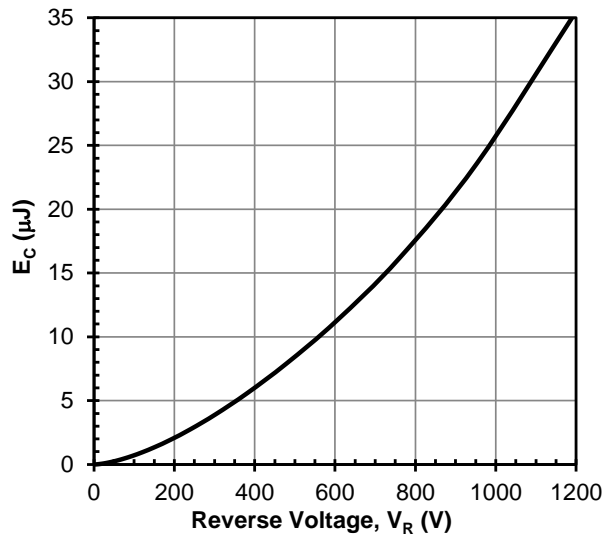
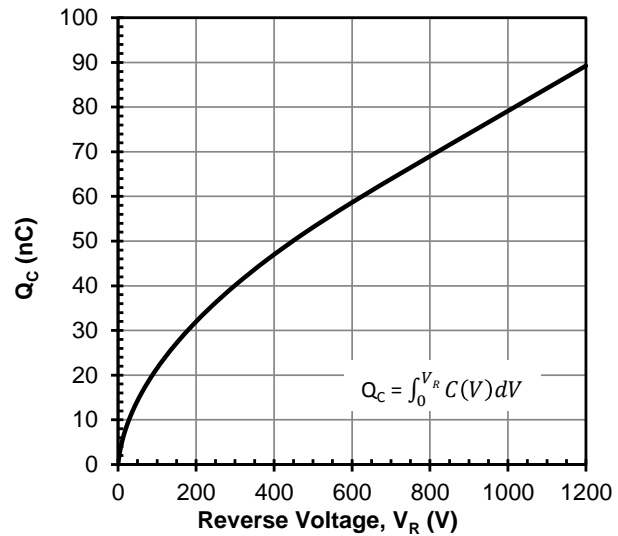


Figure 6 Maximum transient thermal impedance



**Figure 7 Typical capacitance stored energy vs. reverse voltage**



**Figure 8 Typical capacitive charge vs. reverse voltage**

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## We are here for you. Addresses and Contacts.

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### Headquarter Switzerland:

Angst+Pfister Sensors and Power AG  
Thurgauerstrasse 66  
CH-8050 Zurich  
Phone +41 44 877 35 00  
[sensorsandpower@angst-pfister.com](mailto:sensorsandpower@angst-pfister.com)

### Office Germany:

Angst+Pfister Sensors and Power Deutschland GmbH  
Edisonstraße 16  
D-85716 Unterschleißheim  
Phone +49 89 374 288 87 00  
[sensorsandpower.de@angst-pfister.com](mailto:sensorsandpower.de@angst-pfister.com)

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